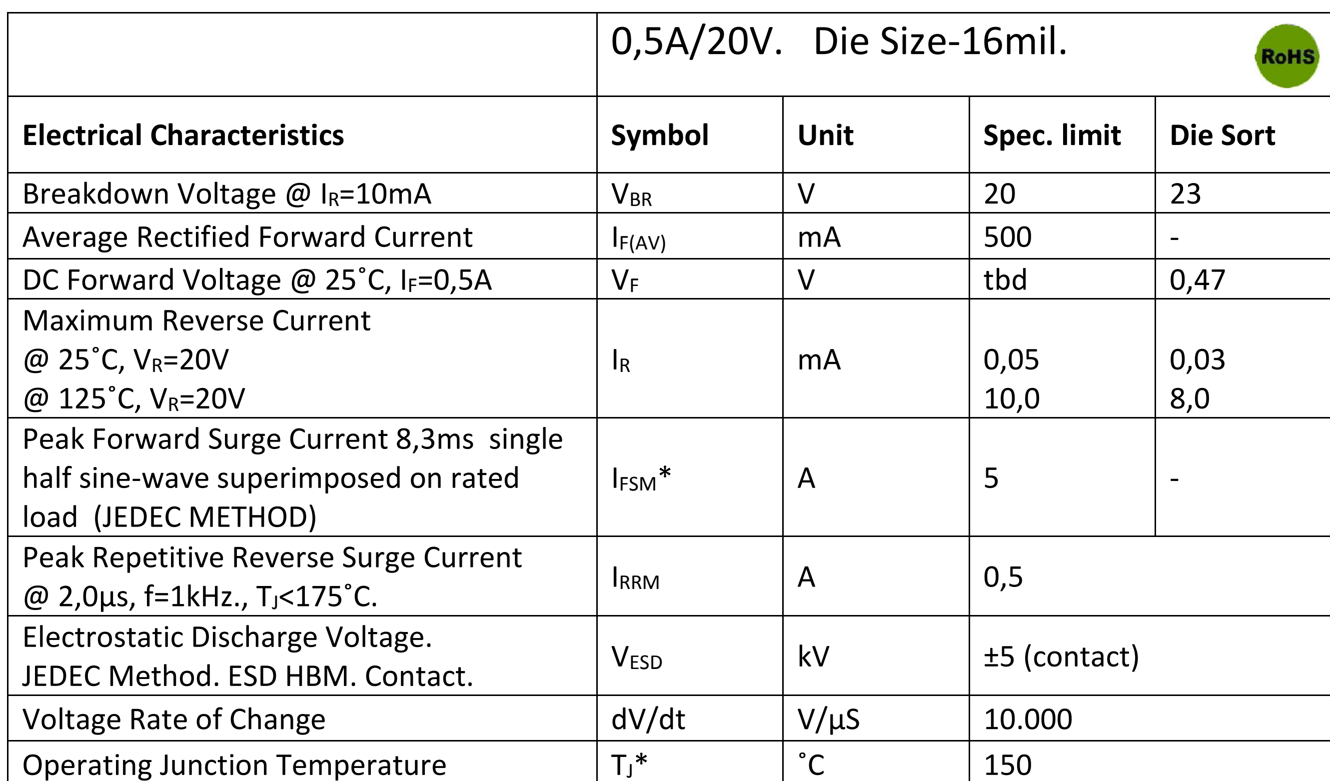
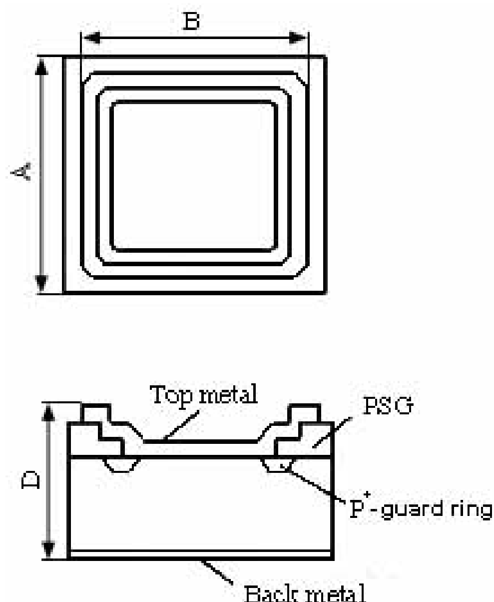
mikron VSP-MIKRON



	0,5A/20V. Die Size-16mil. RoHS			
Electrical Characteristics	**Symbol**	**Unit**	**Spec. limit**	**Die Sort**
Breakdown Voltage @ I_R=10mA	V_{BR}	V	20	23
Average Rectified Forward Current	$I_{F(AV)}$	mA	500	-
DC Forward Voltage @ 25˚C, I_F=0,5A	V_F	V	tbd	0,47
Maximum Reverse Current @ 25˚C, V_R=20V @ 125˚C, V_R=20V	I_R	mA	0,05 10,0	0,03 8,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}*	A	5	-
Peak Repetitive Reverse Surge Current @ 2,0µs, f=1kHz., T_J<175˚C.	I_{RRM}	A	0,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	V_{ESD}	kV	±5 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J*	˚C	150	

* - testing for Devise

* Tj=Ta+Rth(j-a)x(Pf+Pr), where Rth(j-a) – thermal resistance, Pf – forward power dissipation, Pr – revers power dissipation



Mechanical data

DIM	ITEM	µm
A_X A_y	Wafer Form Die Size	410 410
B_X B_y	Top Metal Size	310 310
D	Thickness	245max.
Scribe line Width		40

Top metal:
a) **Al-Ni-Ag** – for Soldering;
b) **Al** – for Wire Bonding.
Backside metal: **Ti-Ni-Ag**.